

Description

The DMP2225L uses advanced trench technology

to provide excellent $R_{\text{DS}(\text{ON})}$, This device is suitable

for use as a load switch or in PWM applications.

General Features

 $V_{DS} = -20V, I_{D} = -3A$

 $R_{DS(ON)} < 80 m\Omega$ @ V_{GS} =-4.5V

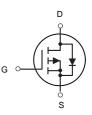
Application

Battery protection

Load switch

Uninterruptible power supply





P-Channel MOSFET

Package Marking and Ordering Information

Product ID	Pack	Brand	Qty(PCS)
DMP2225L	SOT-23	HXY MOSFET	3000

Absolute Maximum Ratings (TA=25 ℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V _{DS}	Drain-Source Voltage	-20	V
V _G s	Gate-Source Voltage	±12	V
l _D	Drain Current-Continuous	-3	А
Ірм	Drain Current-Pulsed (Note 1)	-10	А
P _D	Maximum Power Dissipation	1	W
TJ,Tstg	Operating Junction and Storage Temperature Range	-55 To 150	$^{\circ}$ C
Reja	Thermal Resistance, Junction-to-Ambient (Note 2)	125	°C/W

Electrical Characteristics (T_A=25°C unless otherwise noted)

Parameter	Symbol	Condition	Min	Тур	Max	Unit
Off Characteristics				l	l	
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} =0V I _D =-250μA	-20	-24	-	V
Zero Gate Voltage Drain Current	Ipss	V _{DS} =-20V,V _{GS} =0V	-	-	-1	μA
Parameter	Symbol	Condition	Min	Тур	Max	Unit
Gate-Body Leakage Current	Igss	$V_{GS}=\pm 12V, V_{DS}=0V$	-	-	±100	nA
On Characteristics (Note 3)						
Gate Threshold Voltage	V _{GS} (th)	V _{DS} =V _{GS} , I _D =-250μA	-0.4	-0.7	-1	V
		V _{GS} =-4.5V, I _D =-3A	-	60	80	mΩ
Drain-Source On-State Resistance	RDS(ON)	V _{GS} =-2.5V, I _D =-2A	-	85	103	mΩ
Forward Transconductance	g FS	V _{DS} =-5V, I _D =-2A	5	-	-	S
Dynamic Characteristics (Note4)						
Input Capacitance	Clss		-	405	-	PF
Output Capacitance	Coss	V _{DS} =-10V,V _{GS} =0V,	-	75	-	PF
Reverse Transfer Capacitance	Crss	F=1.0MHz	-	55	-	PF
Switching Characteristics (Note 4)						
Turn-on Delay Time	t d(on)		-	11	-	nS
Turn-on Rise Time	tr	V _{DD} =-10V,I _D =-1A V _{GS} =-	-	35	-	nS
Turn-Off Delay Time	t _{d(off)}	4.5V,R _{GEN} =10Ω	-	30	-	nS
Turn-Off Fall Time	t _f		-	10	-	nS
Total Gate Charge	Qg		-	3.3	12	nC
Gate-Source Charge	Qgs	V _{DS} =-10V, I _D =-3A,	-	0.7	-	nC
Gate-Drain Charge	Qgd	V _{GS} =-2.5V	-	1.3	-	nC
Drain-Source Diode Characteristics			1	1	L	
Diode Forward Voltage (Note 3)	VsD	V _{GS} =0V, I _S =1.3A	-	-	-1.2	V
Diode Forward Current (Note 2)	Is		-	-	-3	Α

Notes:

- 1. Repetitive Rating: Pulse width limited by maximum junction temperature.
- 2. Surface Mounted on FR4 Board, t ≤ 10 sec.
- 3. Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2%.
- 4. Guaranteed by design, not subject to production



Typical Electrical and Thermal Characteristics

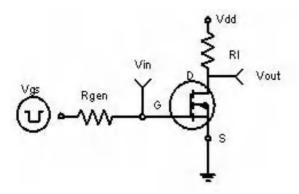


Figure 1:Switching Test Circuit

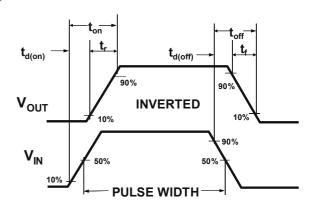


Figure 2:Switching Waveforms

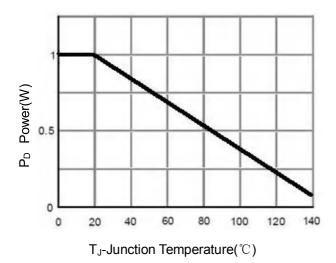
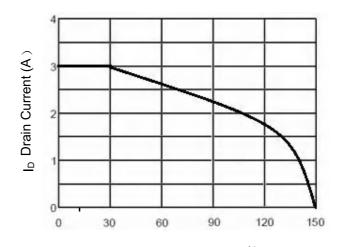


Figure 3 Power Dissipation



T_J-Junction Temperature(°C)
Figure 4 Drain Current

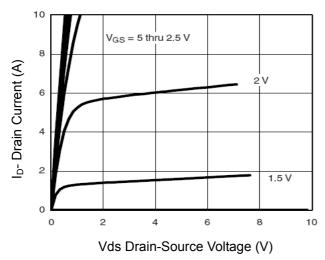


Figure 5 Output Characteristics

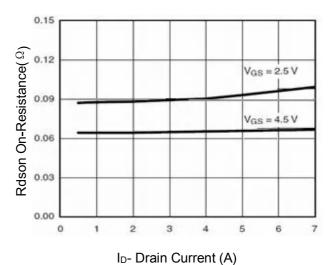
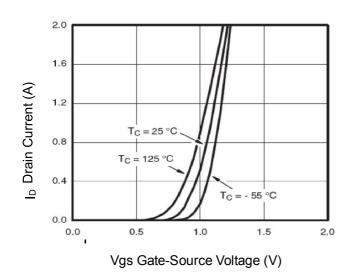


Figure 6 Drain-Source On-Resistance





1.6 V_{GS} = 4.5 V I_D = 3 A 1.2 0.8 0.6 -50 -25 0 25 50 75 100 125 150 T_J-Junction Temperature(°C)



Figure 8 Drain-Source On-Resistance

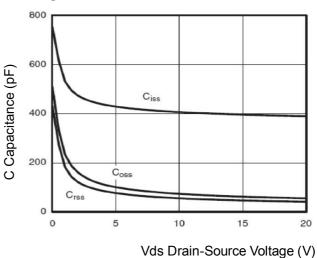
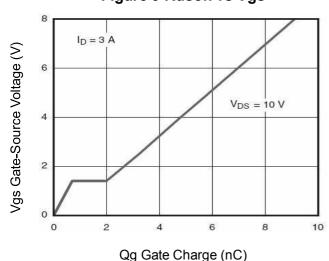


Figure 9 Rdson vs Vgs



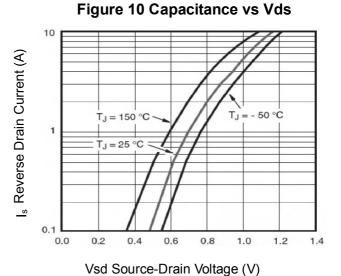
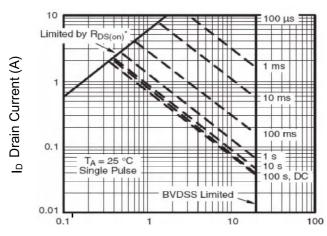


Figure 11 Gate Charge

Figure 12 Source- Drain Diode Forward





Vds Drain-Source Voltage (V)

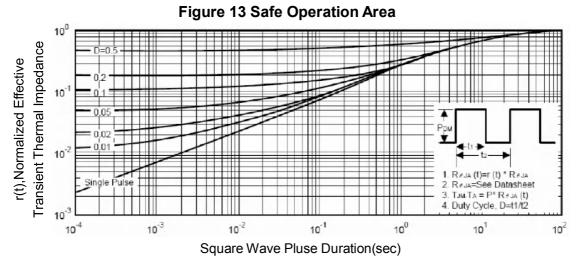
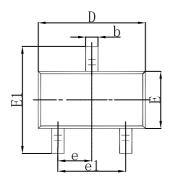
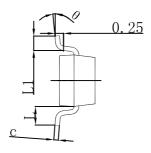


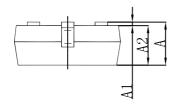
Figure 14 Normalized Maximum Transient Thermal Impedance



SOT-23 Package Outline Dimensions

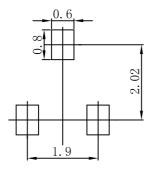






Symbol	Dimensions In Millimeters		Dimensions In Inches		
	Min	Max	Min	Max	
Α	0.900	1.150	0.035	0.045	
A1	0.000	0.100	0.000	0.004	
A2	0.900	1.050	0.035	0.041	
b	0.300	0.500	0.012	0.020	
С	0.080	0.150	0.003	0.006	
D	2.800	3.000	0.110	0.118	
E	1.200	1.400	0.047	0.055	
E1	2.250	2.550	0.089	0.100	
е	0.950 TYP		0.037 TYP		
e1	1.800	2.000	0.071	0.079	
L	0.550 REF		0.022 REF		
L1	0.300	0.500	0.012	0.020	
θ	0°	8°	0°	8°	

SOT-23 Suggested Pad Layout



- Note:
 1.Controlling dimension:in millimeters.
- 2.General tolerance:± 0.05mm.
 3.The pad layout is for reference purposes only.



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